

Violation of Quasineutrality in Semiconductor Transport: The Dember Effect

Maja Krčmar and Wayne M. Saslow

Department of Physics, Texas A&M University, College Station, Texas 77840-4242

Exact solution of the linearized equations for steady-state transport in semiconductors yields two modes that vary exponentially in space, one involving screening (without entropy production) and one involving diffusion and recombination (with entropy production). Neither mode is quasineutral. For constant surface photoexcitation with generation of electrons and holes, the steady-state response is a linear combination of these modes, subject to global electroneutrality. The resultant charge separation produces a voltage difference across the sample (the Dember effect).

The Dember effect is the voltage difference that develops across the bulk of a material that steadily absorbs light at one surface. [1] It has been observed in insulators, [2,3] high resistivity semiconductors, [4,5] and C_{60} thin films. [6] An extensive discussion of photovoltages, both at surfaces and in the bulk, is given in Ref. [7].

An intuitive physical picture of the Dember effect is as follows. [8] Incident light produces equal numbers of electrons and holes at the surface. The higher mobility electrons travel further than the lower mobility holes. The resultant charge separation amounts to a dipole layer. As a consequence the illuminated surface is at the higher voltage, in agreement with experiment. However, conventional theories of the Dember effect, [7,8] which assume quasineutrality (local electroneutrality), yield no dipole layer; moreover, they yield a non-zero net charge.

The present work obtains exact solutions for the surface modes of the linearized macroscopic transport equations. It differs from previous analytic work in that: (1) It explicitly satisfies the principles of irreversible thermodynamics, which constrain the form for the charge-carrier fluxes and recombination rates by the condition that the rate of entropy production be non-negative; (2) In solving the transport equations, it employs both electron and hole densities n and p as variables, rather than assuming deviations from equilibrium satisfy quasineutrality ($\delta n \approx \delta p$); (3) Using the resultant two steady-state surface modes, it explicitly enforces overall electroneutrality.

One surface mode corresponds to ordinary screening by a multi-charge-carrier system (i.e. Debye-Hückel screening), without fluxes or entropy production: the *screening mode*. The other surface mode has both electron and hole flux as well as entropy production: the *diffusion-recombination mode*. The characteristic length l of the screening mode typically is shorter than the characteristic length L for the diffusion-recombination mode. Neither mode is locally electroneutral. Applied to the Dember effect, the light generates a diffusion-recombination mode with a relatively extended negative charge and a screening mode with a relatively compact positive charge, in agreement with the physical picture given above.

Irreversible thermodynamics. Consider a uniform semiconductor with an ideal surface having no extrinsic

surface states and no charged intrinsic states. The recombination rate r is the same for both electrons and holes. With u the energy density, T the temperature, s the entropy density, and $\tilde{\mu}_e$ and $\tilde{\mu}_h$ the electron and hole electrochemical potentials, the fundamental thermodynamic differential for this system is

$$du = Tds + \tilde{\mu}_e dn + \tilde{\mu}_h dp. \quad (1)$$

With μ_e and μ_h the chemical potentials (to be distinguished from the diffusivities μ_n and μ_p),

$$\tilde{\mu}_e \equiv \mu_e - e\phi, \quad \tilde{\mu}_h \equiv \mu_h + e\phi. \quad (2)$$

Here the electrical potential ϕ satisfies Poisson's equation

$$\nabla^2 \phi = -\frac{\rho}{\epsilon_0 \epsilon} = -\frac{e}{\epsilon_0 \epsilon} (p - n + N_d^+ - N_a^-), \quad (3)$$

where ϵ is the semiconductor dielectric constant, ϵ_0 is the permittivity of free space, and the charge density $\rho = e(p - n + N_d^+ - N_a^-)$. N_d^+ and N_a^- are the respective densities of ionized donors and acceptors, and $\tilde{\mu}_e$ and $\tilde{\mu}_h$ are often called quasi-Fermi energies.

The conservation laws for this system are

$$\partial_t u + \partial_i j_i^u = 0, \quad \partial_t s + \partial_i j_i^s = \frac{\mathcal{P}}{T} \geq 0, \quad (4)$$

$$\partial_t n + \partial_i j_i^n = r, \quad \partial_t p + \partial_i j_i^p = r. \quad (5)$$

Here j_i^u is the energy flux density, j_i^s is the entropy flux density, $\mathcal{P}$ is the local rate of heat production ($\mathcal{P}/T$ is local rate of entropy production), j_i^n is the electron number flux density, and j_i^p is the hole number flux density. The fluxes, r , and $\mathcal{P}$ are to be determined.

The time-derivatives of (1) and (4)–(5) lead to

$$\begin{aligned} 0 \leq \mathcal{P} &= -\partial_i j_i^u + T \partial_i j_i^s - \tilde{\mu}_e (r - \partial_i j_i^n) - \tilde{\mu}_h (r - \partial_i j_i^p) \\ &= -\partial_i (j_i^u - T j_i^s - \tilde{\mu}_e j_i^n - \tilde{\mu}_h j_i^p) \\ &\quad - j_i^s \partial_i T - j_i^n \partial_i \tilde{\mu}_e - j_i^p \partial_i \tilde{\mu}_h - r(\tilde{\mu}_e + \tilde{\mu}_h). \end{aligned} \quad (6)$$

Expressing $\mathcal{P}$ as a non-negative quadratic form requires that $j_i^u = T j_i^s + \tilde{\mu}_e j_i^n + \tilde{\mu}_h j_i^p$; that

$$j_i^s = -\alpha_T \partial_i T = -\frac{\kappa}{T} \partial_i T, \quad (7)$$

where $\kappa \geq 0$ is the thermal conductivity; that

$$\begin{aligned} j_i^n &= -\alpha_{nn}\partial_i\tilde{\mu}_e - \alpha_{np}\partial_i\tilde{\mu}_h, \\ j_i^p &= -\alpha_{pn}\partial_i\tilde{\mu}_e - \alpha_{pp}\partial_i\tilde{\mu}_h, \end{aligned} \quad (8)$$

where $\alpha_{nn} \geq 0, \alpha_{pp} \geq 0$, and $\alpha_{nn}\alpha_{pp} \geq \alpha_{np}\alpha_{pn}$ (the α 's are related to the diffusivities, and $\alpha_{np} = \alpha_{pn}$ by the Onsager symmetry principle [9]); and that

$$r = -\lambda(\tilde{\mu}_e + \tilde{\mu}_h) = -\lambda(\mu_e + \mu_h). \quad (9)$$

where $\lambda \geq 0$ is related to the electron and hole lifetimes τ_n and τ_p . In equilibrium $r = 0$, so (9) implies the well-known results that $\tilde{\mu}_e = -\tilde{\mu}_h$ and $\mu_e = -\mu_h$ in equilibrium. We now express r , j_i^n , and j_i^p in more conventional form.

Linearizing (9) about equilibrium with $\delta\mu_e = (\partial\mu_e/\partial n)\delta n$ and $\delta\mu_h = (\partial\mu_h/\partial p)\delta p$ yields

$$r = -\frac{\delta n}{\tau_n} - \frac{\delta p}{\tau_p}, \quad \tau_n^{-1} \equiv \lambda \frac{\partial\mu_e}{\partial n}, \quad \tau_p^{-1} \equiv \lambda \frac{\partial\mu_h}{\partial p}. \quad (10)$$

For a dilute semiconductor, as considered here, $(\partial\mu_e/\partial n) \approx k_B T/n_0$ and $(\partial\mu_h/\partial p) \approx k_B T/p_0$, so $\tau_n = (n_0/k_B T\lambda)$ and $\tau_p = (p_0/k_B T\lambda)$.

Now set $\alpha_{np} = \alpha_{pn} \approx 0$, $\alpha_{nn} = D_n(\partial n/\partial\mu_e)$, and $\alpha_{pp} = D_p(\partial p/\partial\mu_h)$, where D_n and D_p are the electron and hole diffusivities. Next, define the electron and hole mobilities μ_n and μ_p , which satisfy the Einstein relations:

$$\mu_n = \frac{eD_n}{n} \frac{\partial n}{\partial\mu_e} \approx \frac{eD_n}{k_B T}, \quad \mu_p = \frac{eD_p}{p} \frac{\partial p}{\partial\mu_h} \approx \frac{eD_p}{k_B T}, \quad (11)$$

Then in one-dimension j_i^n and j_i^p become [10,11]

$$\begin{aligned} j_x^n &= -D_n \partial_x n + \mu_n n \partial_x \phi, \\ j_x^p &= -D_p \partial_x p - \mu_p p \partial_x \phi. \end{aligned} \quad (12)$$

Note that Poisson's equation linearizes to

$$\begin{aligned} \nabla^2 \delta\phi &= -\frac{e}{\epsilon_0 \epsilon} (\delta p - \delta n) = \frac{e^2}{\epsilon_0 \epsilon} \left(\frac{\partial n}{\partial\mu_e} + \frac{\partial p}{\partial\mu_h} \right) \delta\phi \\ &\quad - \frac{e}{\epsilon_0 \epsilon} \left(\frac{\partial p}{\partial\mu_h} \delta\tilde{\mu}_h - \frac{\partial n}{\partial\mu_e} \delta\tilde{\mu}_e \right). \end{aligned} \quad (13)$$

Static surface solutions in one-dimension. One steady-state solution that automatically satisfies (5), (8), and (9) has $\delta\tilde{\mu}_e = \delta\tilde{\mu}_h = 0$ and $j_i^n = j_i^p = 0$. Thus the system is in local equilibrium, with no entropy production. This corresponds to ordinary screening, and thus we call it the *screening mode*, with subscript S . From (13), its potential $\delta\phi_S$ satisfies

$$\nabla^2 \delta\phi_S = \frac{e^2}{\epsilon_0 \epsilon} \left(\frac{\partial p}{\partial\mu_h} + \frac{\partial n}{\partial\mu_e} \right) \delta\phi_S = q_S^2 \delta\phi_S, \quad (14)$$

where

$$q_S^2 = q_{Sn}^2 + q_{Sh}^2, \quad q_{Sn}^2 \equiv \frac{e^2}{\epsilon_0 \epsilon} \frac{\partial n}{\partial\mu_e}, \quad q_{Sp}^2 \equiv \frac{e^2}{\epsilon_0 \epsilon} \frac{\partial p}{\partial\mu_h}. \quad (15)$$

For the present system, $q_{Sn}^2 = (e^2 n_0 / \epsilon_0 \epsilon k_B T)$, $q_{Sp}^2 = (e^2 p_0 / \epsilon_0 \epsilon k_B T)$, so $q_S^2 = (e^2 / \epsilon_0 \epsilon k_B T)(n_0 + p_0)$. The solution to (14) that goes to zero as $x \rightarrow \infty$ is

$$\delta\phi_S = A_S \exp(-q_S x). \quad (16)$$

$l \equiv q_S^{-1}$ is the *screening length*. From (16) and (13), the screening mode has charge density

$$\delta\rho_S = -\epsilon_0 \epsilon \nabla^2 \phi_S = -(\epsilon_0 \epsilon) q_S^2 A_S \exp(-q_S x). \quad (17)$$

Here $\delta n_S = (\partial n / \partial\mu_e) \delta\mu_e = (en_0 / k_B T) \delta\phi_S$ and $\delta p_S = (\partial p / \partial\mu_h) \delta\mu_h = -(en_0 / k_B T) \delta\phi_S$, so $\delta n_S / \delta p_S = -n_0 / p_0$.

The second steady-state solution to (5), (8), (9) and (13) has $\delta\tilde{\mu}_e$ and $\delta\tilde{\mu}_h$ non-zero, so the fluxes j_i^n and j_i^p are non-zero. With $\alpha_{np} = \alpha_{pn} = 0$, combining (5), (8) and (9) yields

$$\begin{aligned} -\alpha_{nn} \partial_x^2 \delta\tilde{\mu}_e &= -\lambda(\delta\tilde{\mu}_e + \delta\tilde{\mu}_h), \\ -\alpha_{pp} \partial_x^2 \delta\tilde{\mu}_h &= -\lambda(\delta\tilde{\mu}_e + \delta\tilde{\mu}_h). \end{aligned} \quad (18)$$

Let us denote properties of this *diffusion-recombination mode* by the subscript D . Now set

$$q_{Dn}^2 \equiv \frac{\lambda}{\alpha_{nn}} = \frac{1}{D_n \tau_n}, \quad q_{Dp}^2 \equiv \frac{\lambda}{\alpha_{pp}} = \frac{1}{D_p \tau_p}. \quad (19)$$

Then, with

$$\delta\tilde{\mu}_e = A_{Dn} \exp(-q_D x), \quad \delta\tilde{\mu}_h = A_{Dp} \exp(-q_D x), \quad (20)$$

(18) yields

$$q_D^2 = q_{Dn}^2 + q_{Dp}^2 \quad (21)$$

and $A_{Dp}/q_{Dp}^2 = A_{Dn}/q_{Dn}^2$.

The corresponding electrostatic potential $\delta\phi_D$ takes the form

$$\delta\phi_D = A_D \exp(-q_D x), \quad (22)$$

where

$$\frac{A_{Dp}}{q_{Dp}^2} = \frac{A_{Dn}}{q_{Dn}^2} = \frac{q_S^2 - q_D^2}{q_{Sp}^2 q_{Dp}^2 - q_{Sn}^2 q_{Dn}^2} e A_D. \quad (23)$$

$L \equiv q_D^{-1}$ is the *diffusion-recombination length*, normally called the diffusion length. By (22) and (3), the diffusion-recombination mode possesses charge density

$$\delta\rho_D = -(\epsilon_0 \epsilon) q_D^2 A_D \exp(-q_D x). \quad (24)$$

Moreover, $\delta n_D / \delta p_D = (n_0 / p_0)(q_{Sp}^2 - q_{Dn}^2) / (q_{Sn}^2 - q_{Dp}^2)$. This is independent of n_0 for fixed $n_0 p_0 = n_i^2$.

Surface mode amplitudes. Let light incident at the surface $x = 0$ produce equal electron and hole fluxes G , so $j_i^n = j_i^p = G$ at $x = 0$. On setting $\alpha_{np} = \alpha_{pn} = 0$, (8) and (20) yield the diffusion-recombination mode amplitudes

$$A_{Dn} = \frac{G}{q_D \alpha_{nn}}, \quad A_{Dp} = \frac{G}{q_D \alpha_{pp}}. \quad (25)$$

Overall electroneutrality, or $0 = \int_0^\infty dx(\delta\rho_S(x) + \delta\rho_D(x))$, implies that

$$A_S = -\frac{q_D}{q_S} A_D. \quad (26)$$

From (17) and (26), and from (23-25), the total charge density is

$$\delta\rho(x) = \frac{Ge^2}{k_B T} \frac{(\mu_n - \mu_p)}{\mu_n \mu_p} \frac{q_S e^{-q_S x} - q_D e^{-q_D x}}{q_S^2 - q_D^2}, \quad (27)$$

where the mobilities have been employed. Typically $\mu_n > \mu_p$, so $\rho(x=0)$ is positive, as expected if the higher mobility charge-carrier preferentially leaves the vicinity of the surface. Note that $\delta\rho(x)$ changes in sign as x increases, as needed to produce a dipole layer.

From (17) and (24), the total electrostatic potential is

$$\delta\phi(x) = \frac{Ge^2}{\epsilon_0 \epsilon k_B T} \frac{(\mu_n - \mu_p)}{\mu_n \mu_p} \frac{q_D^{-1} e^{-q_D x} - q_S^{-1} e^{-q_S x}}{q_S^2 - q_D^2}. \quad (28)$$

To compare with experiment, (28) gives the Dember voltage $\phi_{Dem} \equiv \delta\phi(x=0)$ as

$$\phi_{Dem} = \frac{Ge^2}{\epsilon_0 \epsilon k_B T} \frac{(\mu_n - \mu_p)}{\mu_n \mu_p} \frac{1}{q_S q_D} \frac{1}{q_S + q_D}. \quad (29)$$

Discussion. Eq.(29) makes numerous predictions. First, since typically $\mu_n > \mu_p$, ϕ_{Dem} is positive, as expected for a dipole layer with positive charge closer to the surface. Further, since typically $q_D \ll q_S$, the term $q_S q_D (q_S + q_D) \approx q_S^2 q_D$. The dependences of q_S on n and ϵ , and of q_D on μ and τ , show that ϕ_{Dem} varies inversely with carrier density n , as the square root of the characteristic recombination time τ , as the inverse square root of the characteristic mobility μ , and is independent of ϵ .

The dependence on n explains why ϕ_{Dem} is observed in materials with relatively low carrier densities. The dependence on τ indicates that ϕ_{Dem} is larger for longer recombination times; the dependence on μ indicates that ϕ_{Dem} is larger for lower mobilities.

Figures 1-4 are computed for an intrinsic semiconductor with equilibrium carrier number density $n_0 = p_0 = n_i = 10^{16} \text{ m}^{-3}$, recombination time $\tau = 10^{-5} \text{ s}$, electron mobility $\mu_n = 1000 \text{ cm}^2/(\text{V}\cdot\text{s})$, hole mobility $\mu_p = 200 \text{ cm}^2/(\text{V}\cdot\text{s})$, room temperature $k_B T = 0.0253 \text{ eV}$, and dielectric constant $\epsilon = 10$. These values give $l = 26.4 \text{ }\mu\text{m}$ and $L = 64.8 \text{ }\mu\text{m}$. From (28), the ratio of the contributions of the diffusion mode and the screening mode to the Dember voltages is $q_D^{-1}/q_S^{-1} = L/l$. Taking $G = 10^{17} \text{ m}^{-2}\text{s}^{-1}$ gives $\phi_{Dem} = 9.22 \text{ mV}$, of which the diffusion mode is responsible for 15.56 mV and the screening mode -6.34 mV . The theory, which is valid for $\delta\tilde{\mu}_e$ and $\delta\tilde{\mu}_h$ small relative to $k_B T$, becomes invalid for significantly larger G .

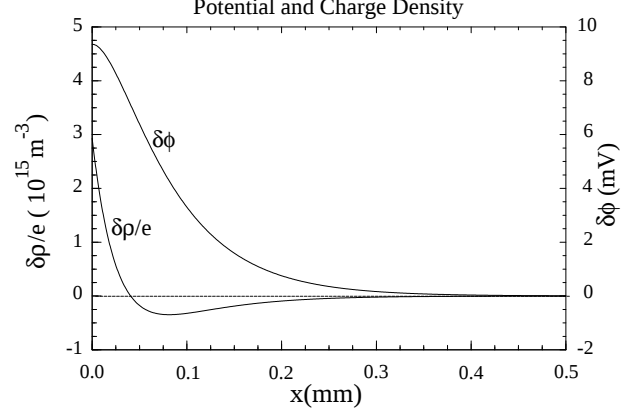


FIG. 1. Photo-induced electrical potential $\delta\phi$ from (28) and charge density $\delta\rho$ from (27).

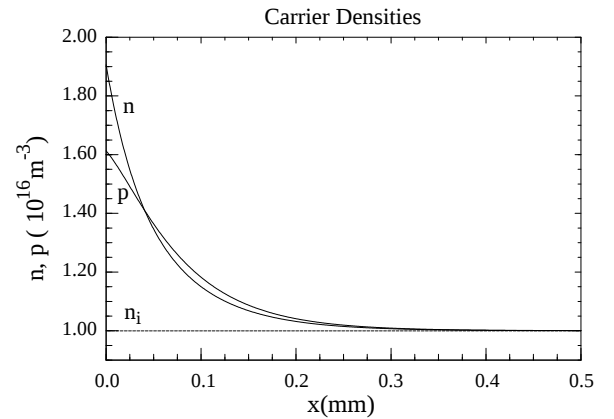


FIG. 2. Electron and hole number densities n and p corresponding to Figure 1.

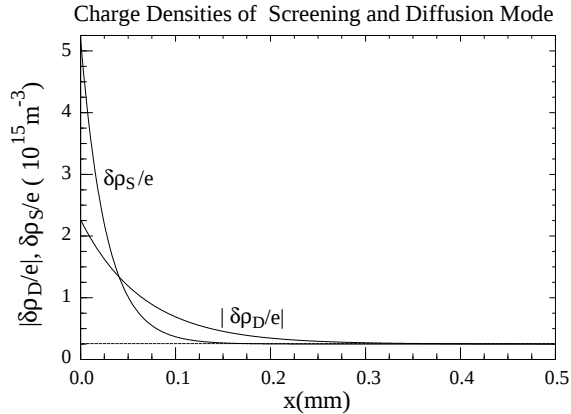


FIG. 3. Charge densities for the screening and diffusion modes, from (17) and (24).

Fig.1 presents $\delta\phi$ and $\delta\rho$. Note that $\delta\phi$ is monotonic, whereas $\delta\rho$ changes sign, so that the system can be overall neutral. Fig.2 presents the number densities n and p associated with $\delta\rho$ of Fig.1. The curves sketched (but not computed) in Ref. [8] (Fig.V.3) agree qualitatively with Figs.1 and 2.

The individual charge densities ρ due to the diffusion-recombination and screening modes are presented in Fig.3. Note that $\delta n_S/\delta p_S = -1$ and $\delta n_D/\delta p_D = 1.306$ for the present parameters. (Increasing both mobilities by a factor of ten would give $\delta n_D/\delta p_D = 1.022$.) Hence quasineutrality is not a good approximation for either mode. The charge density for the screening mode is positive and concentrated near the surface, whereas the charge density for the diffusion-recombination mode is negative and more extended. Note that numerical solutions of the macroscopic transport equations for semiconductors normally do not assume quasineutrality, so they retain the full physics. [12] However, they do not permit extensive physical interpretation.

Fig.4 presents the bulk charge density $\delta\rho$ for μ_n and μ_p as above ($\mu_p/\mu_n = 0.2$), and for three additional values of μ_p/μ_n . $\delta\rho$ and ϕ_{Dem} increase with the difference in the electron and hole mobilities.

Surface solutions also are relevant to current flow across interfaces. Already in the nineteenth century, Maxwell noted that for current flow between two single-carrier materials charge builds up at the interface; however, without a more microscopic theory it is not possible to determine how much charge is associated with each material. A similar effect must occur at a semiconductor-metal interface, even without the complexities associated with modification of the Schottky barrier. Surface solutions likely are present in recent numerical studies showing that spin injection in a semiconductor (e.g., by preferential absorption of polarized light) persists across a

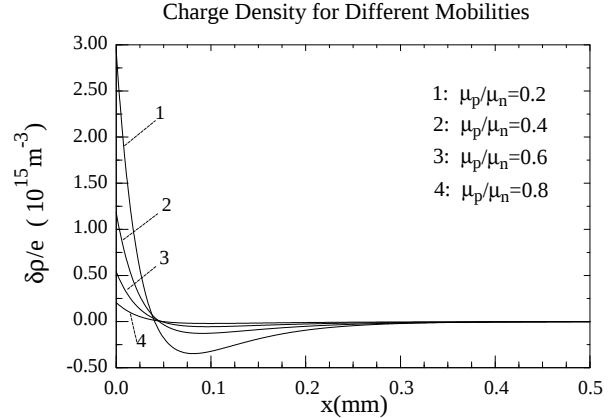


FIG. 4. Charge density $\delta\rho$ from (27) for different hole mobilities.

$p-n$ junction. [13] Such a system, with up and down electrons and with unpolarized holes, should have three surface modes: one screening mode and two diffusion-recombination modes. The rapid falloff of spin polarization at one end of the system is evidence for surface solutions induced by what the authors of Ref. [13] consider to be an artificial boundary condition.

The present multi-carrier system, with a finite diffusion-recombination length L , is non-neutral only over a finite distance from the disturbance. On the other hand, a multi-carrier system with no recombination (and thus $L \rightarrow \infty$) can be non-neutral in the bulk, far from a disturbance. [14]

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- [1] H. Dember, Phys.Z. **32**, 554 (1931); H. Dember, Phys.Z. **33**, 207 (1932).
 - [2] Hartmut Kallmann, Bernard Kramer, Julius Shain and Grace Marmor Spruch, Phys. Rev. **117**, 1482 (1959).
 - [3] Bernard Kramer, John T. Wallmark and Peter Mark, J. Vac. Sci. Technol. **12**, 713 (1975).
 - [4] G. Badics and Z. Szalmassy, Phys. Lett. **69 A**, 365 (1997).
 - [5] W.F. Berg, E. Blum, J. Decker and O. Martin, Zeit. Phys. Chem. **108**, 123 (1977).
 - [6] Dipankar Sarkar and N. J. Halas, Sol. Stat. Com. **90**, 261 (1994).
 - [7] Leor Kronik and Yoram Shapira, Surface Science Reports **37**, 1 (1999).
 - [8] Jean-Noël Chazalviel, *Coulomb Screening by Mobile*

Charges, Birkhäuser, Boston (1999).

- [9] L.D. Landau and E.M. Lifshitz, *Statistical Physics*, 2nd edition, Addison-Wesley, Reading, MA (1969). See pp.374-378.
- [10] Neil W. Ashcroft and N. David Mermin, *Solid State Physics*, Holt, Rinehart and Winston, New York (1975).
- [11] S.M. Sze, *Physics of Semiconductor Devices*, John Wiley & Sons, New York (1981).
- [12] C.E. Korman and I.D. Mayergoyz, J. Appl. Phys. **68**, 1324 (1990).
- [13] I. Zutic, J. Fabian, and S. Das Sarma, preprint (arXiv:cond-mat/0103473).
- [14] W.M. Saslow, Phys. Rev. Lett. **76**, 4849 (1996).